**ISEN Booster Award Summary Slide:**

“Mechanisms of Resistance Change in Oxides for Non-Volatile Memory”

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In-Situ TEM Biasing of FIB-Thinned Pt/Ti-doped NiOₓ/Pt

Electrical Probing of 10×10 µm², Pt/Ti-doped NiOₓ/Pt

Results:

- Local changes in microstructure are correlated with electroforming
- Both unipolar and bipolar resistance switching types can be observed